

SPIN-CURRENT SWITCHED MAGNETIC MEMORY ELEMENT
SUITABLE FOR CIRCUIT INTEGRATION AND METHOD
OF FABRICATING THE MEMORY ELEMENT

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ABSTRACT

10 A magnetic memory element switchable by current injection includes a plurality of
magnetic layers, at least one of the plurality of magnetic layers having a perpendicular magnetic
anisotropy component and including a current-switchable magnetic moment, and at least one
barrier layer formed adjacent to the plurality of magnetic layers (e.g., between two of the
magnetic layers). The memory element has the switching threshold current and device
15 impedance suitable for integration with complementary metal oxide semiconductor (CMOS)
integrated circuits.

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